

Development of a Pixelated Ultra-Light Double-Sided Ladder for Future Vertex Detectors

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on behalf of the CMOS-ILC team of IPHC/Strasbourg

▶ more information on IPHC Web site: <http://www.iphc.cnrs.fr/-CMOS-ILC-.html>

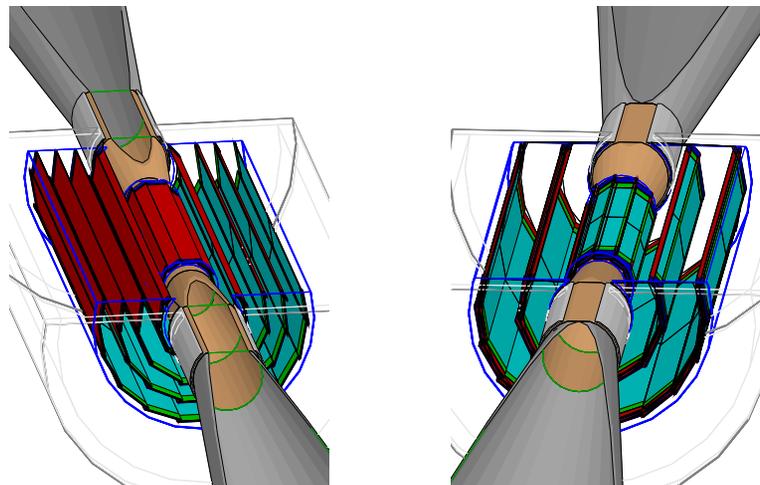
Contents

- Major outcome of 11 years of CMOS pixel sensor R&D at IPHC:
 - ▶ Achieved performances
 - ▶ Applications under way
 - ▶ Plans → 2012/13
- Perspectives for a future vertex detector adapted to EIC:
 - ▶ Objectives
 - ▶ Deliverables
 - ▶ Context
- Summary



- Sensor requirements defined w.r.t. ILD VTX geometries

- * 2 alternative geometries :
 - ◇ 5 single-sided layers
 - ◇ 3 double-sided layers (mini-vectors)
- * pixel array read-out perpendicular to beam lines



- Prominent specifications :

- * read-out time target values (continuous read-out version) :

SL1/SL2 /SL3 /SL4 /SL5

DL1 / DL2 / DL3

- ◇ single-sided : 25 / 50 / 100 / 100 / 100 μs

- ◇ double-sided : 25–25 / 100–100 / 100–100 μs

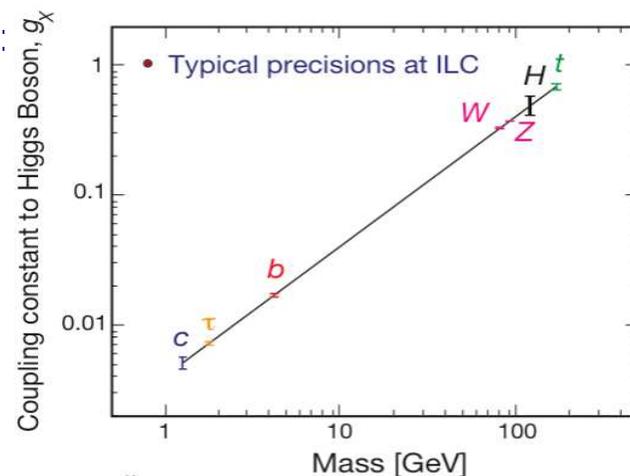
- * $\sigma_{sp} < 3 \mu m$ (partly with binary outputs) \Rightarrow resolution on vertex position $\sim O(10) \mu m$

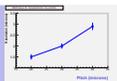
- * ladder material budget in sensitive area ($\lesssim 50 \mu m$ thin sensors) :

- ◇ single-sided : $< 0.2 \% X_0$

- ◇ double-sided : $\sim 0.2 \% X_0$

- * $P_{diss} \lesssim 0.1-2 W/cm^2$

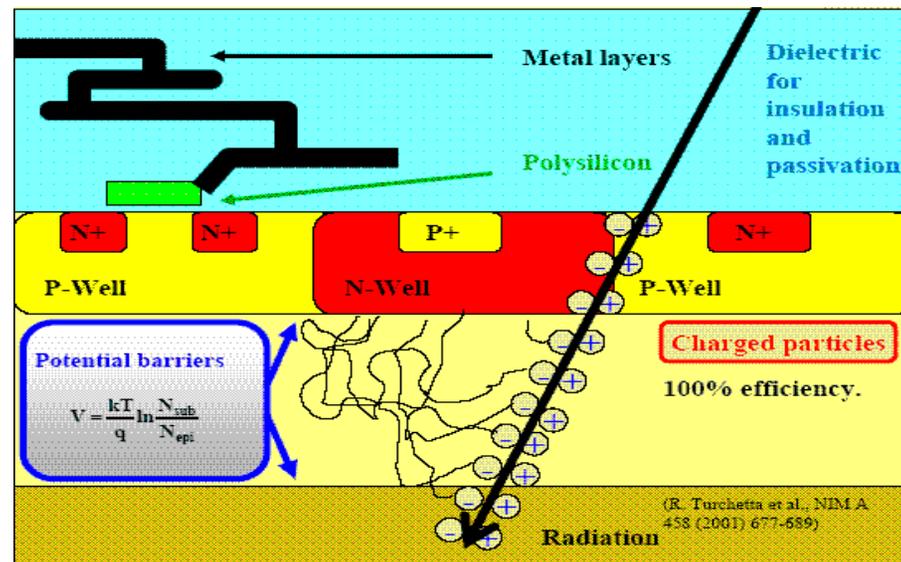




Main Features and Advantages of CMOS Sensors

- P-type low-resistivity Si hosting n-type "charge collectors"

- signal created in epitaxial layer (low doping):
 $Q \sim 80 \text{ e-h} / \mu\text{m} \mapsto \text{signal} \lesssim 1000 \text{ e}^-$
- charge sensing through n-well/p-epi junction
- excess carriers propagate (thermally) to diode with help of reflection on boundaries with p-well and substrate (high doping)

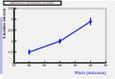


- Prominent advantages of CMOS sensors:

- ◇ granularity: pixels of $\lesssim 10 \times 10 \mu\text{m}^2 \Rightarrow$ high spatial resolution
- ◇ low mat. budget: sensitive volume $\sim 10 - 15 \mu\text{m} \Rightarrow$ total thickness $\lesssim 50 \mu\text{m}$
- ◇ signal processing μ circuits integrated in the sensors \Rightarrow compacity, high data throughput, flexibility, etc.
- ◇ other attractive aspects: cost, multi-project run frequency, T_{room} operation, etc.

▷ ▷ ▷ Attractive balance between granularity, mat. budget, rad. tolerance, r.o. speed & power dissipation

- Limitations:
 - ✗ Very thin sensitive volume \mapsto impact on signal magnitude (mV !) \Rightarrow vey low noise FEE
 - ✗ Sensitive volume almost undepleted \Rightarrow impact on radiation tolerance & speed
 - ✗ Commercial fab. \Rightarrow fab. param. (doping profile, etc.) not optimal for charged part. detection
 - ✗ etc.

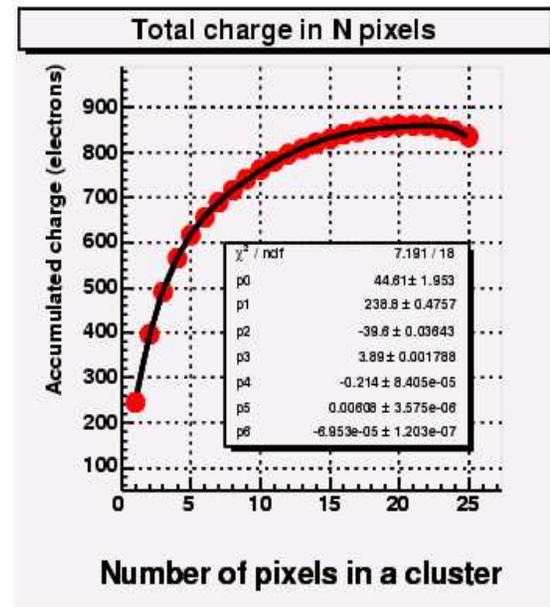
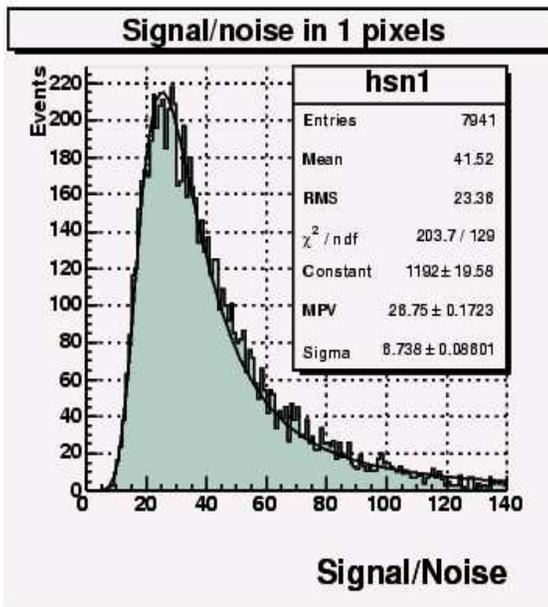
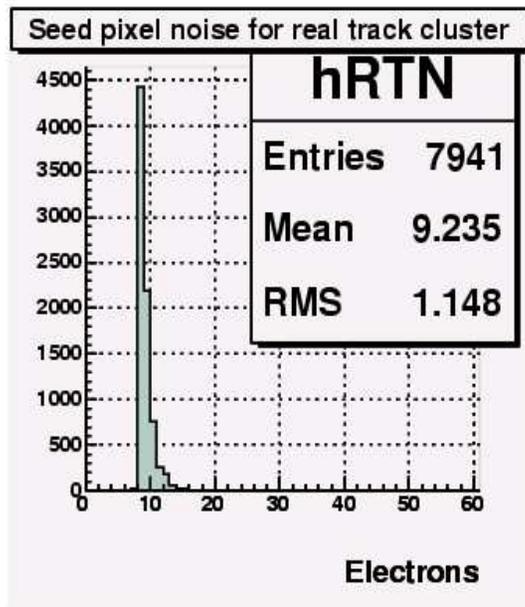


Achieved Performances

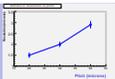
with Analog Output Sensors



- ~ 30 different prototypes designed at IPHC (some with IRFU/Saclay)
- ~ 100 chips tested on H.E. beams since 2001 at CERN & DESY, mounted on Si-strip or pixel telescope
 ⇒ **well established performances (analog output):**
 - * Example of well performing technology: AMS 0.35 μm OPTO \rightarrow ~ 14 & 20 μm epitaxy thickness
 - * $N \sim 10 e^- \text{ ENC} \mapsto S/N \gtrsim 20 - 30$ (MPV) at room Temperature



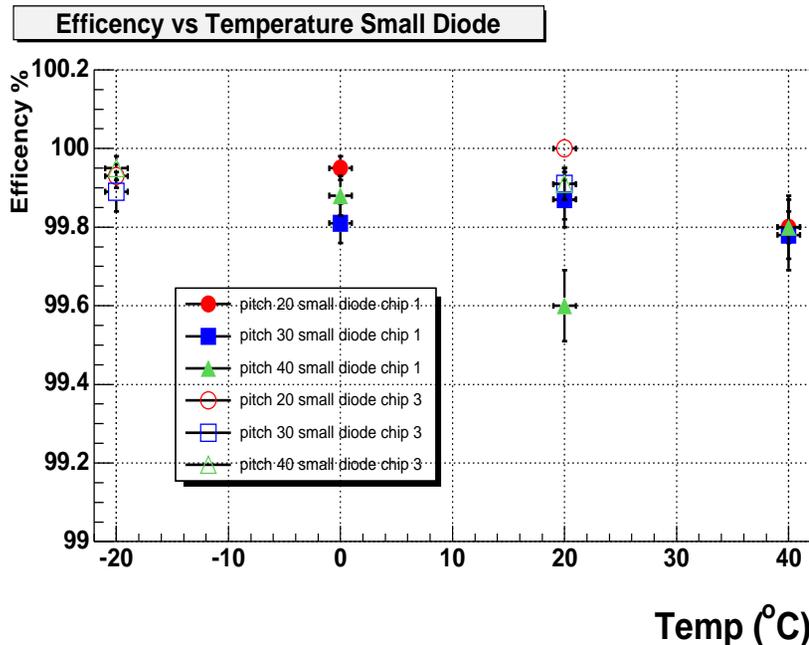
- * Macroscopic sensors : MIMOSA-5 (~ 1.7x1.7 cm²; 1 Mpix) ; MIMOSA-20 (1x2 cm²; 200 kpix) ; MIMOSA-17 (0.76x0.76 cm²; 65 kpix) ; MIMOSA-18 (0.55x0.55 cm²; 256 kpix)



Detection Efficiency & Spatial Resolution

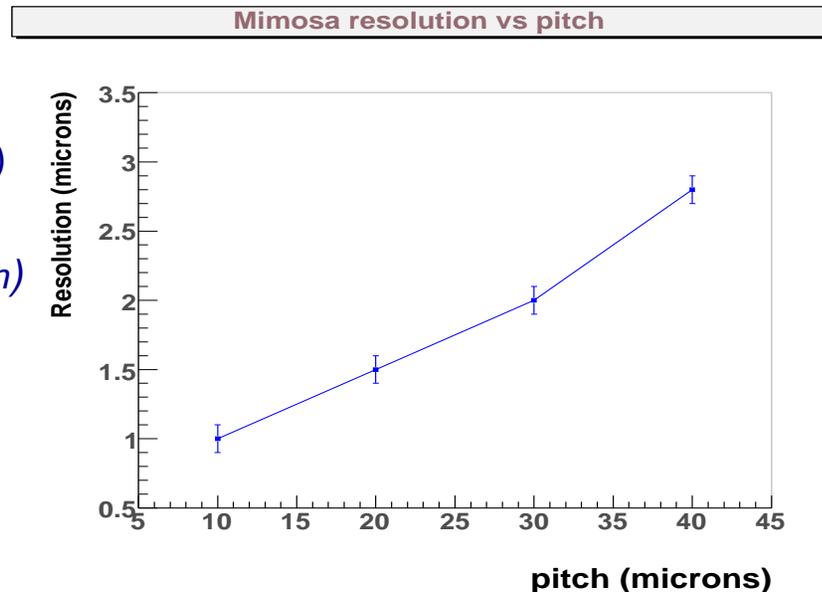
● Detection efficiency:

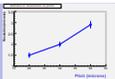
- * Ex: MIMOSA-9 data (20, 30 & 40 μm pitch)
- * $\epsilon_{det} \gtrsim 99.5\text{--}99.9\%$ repeatedly observed at room temperature (fake rate $\sim 10^{-5}$)
- * $T_{oper.} \gtrsim 40^\circ\text{C}$



● Single point resolution versus pixel pitch:

- * clusters reconstructed with eta-function, exploiting charge sharing between pixels (12-bit ADC)
- * $\sigma_{sp} \sim 1 \mu\text{m}$ (10 μm pitch) $\rightarrow \lesssim 3 \mu\text{m}$ (40 μm pitch)
- * 4-bit ADC simul. $\Rightarrow \sigma_{sp} \lesssim 2 \mu\text{m}$ (20 μm pitch)
- * measured binary output resolution (MIMOSA-16, -22): $\sigma_{sp} \gtrsim 3.5$ & $4.5 \mu\text{m}$ (18.4 & 25 μm pitch)





Radiation Tolerance: Condensed Summary

● Ionising radiation tolerance (chips irradiated with 10 keV X-Rays) :

✳ Pixels modified against hole accumulations (thick oxide) and leakage current increase (guard ring)

✳ MIMOSA-15 tested with $\sim 5 \text{ GeV } e^-$ at DESY after 10 kGy exposure : Preliminary results

- $T = -20^\circ\text{C}$, $t_{r.o.} \sim 180 \mu\text{s}$
- $t_{r.o.} \ll 1\text{ms}$ crucial at T_{room}

Integ. Dose	Noise	S/N (MPV)	Detection Efficiency
0	9.0 ± 1.1	27.8 ± 0.5	100 %
1 MRad	10.7 ± 0.9	19.5 ± 0.2	$99.96 \pm 0.04 \%$

● Non-ionising radiation tolerance (chips irradiated with O(1 MeV) neutrons):

✳ MIMOSA-15 (20 μm pitch) tested on DESY e^- beams : Preliminary results

- $T=-20^\circ\text{C}$, $t_{r.o.} \sim 700\mu\text{s}$
- $5.8 \cdot 10^{12} \text{ n}_{eq}/\text{cm}^2$ values with **standard** & **soft** cuts

Fluence ($10^{12} \text{ n}_{eq}/\text{cm}^2$)	0	0.47	2.1	5.8 (5/2)	5.8 (4/2)
S/N (MPV)	27.8 ± 0.5	21.8 ± 0.5	14.7 ± 0.3	$8.7 \pm 2.$	$7.5 \pm 2.$
Det. Efficiency (%)	100.	99.9 ± 0.1	99.3 ± 0.2	$77. \pm 2$	$84. \pm 2.$

✳ MIMOSA-18 (10 μm pitch) tested at CERN-SPS (120 GeV π^- beam) : Preliminary results

- $T = -20^\circ\text{C}$, $t_{r.o.} \sim 3 \text{ ms}$

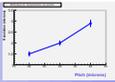
○ parasitic 1–2 kGy γ gas \Rightarrow N ↗

Fluence ($\text{ n}_{eq}/\text{cm}^2$)	0	$6 \cdot 10^{12}$	$1 \cdot 10^{13}$
$Q_{clust} (e^-)$	1026	680	560
S/N (MPV)	28.5 ± 0.2	20.4 ± 0.2	14.7 ± 0.2
Det. Efficiency (%)	99.93 ± 0.03	99.85 ± 0.05	99.5 ± 0.1

● Conclusion :

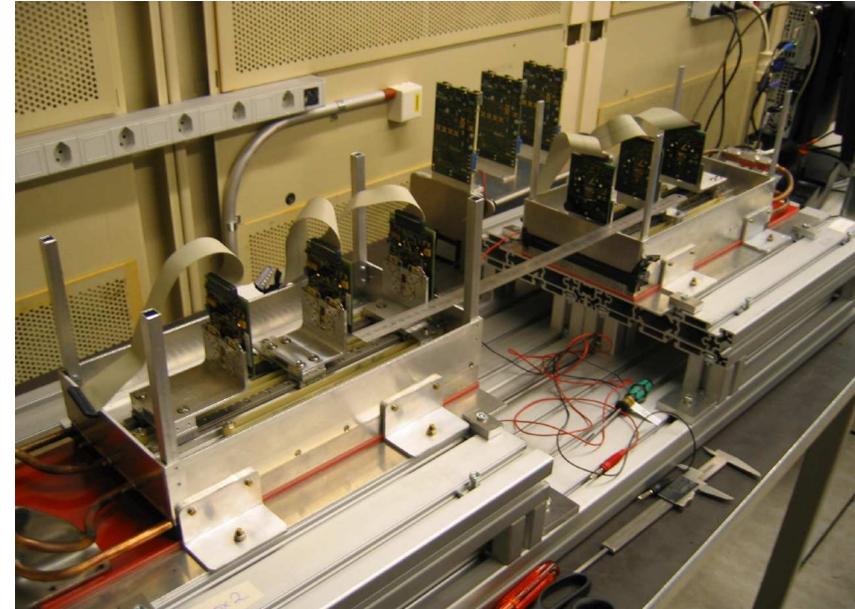
✳ observed ionising radiation tolerance: O(10 kGy)

✳ observed non-ionising rad. tol.: $> 1 \cdot 10^{13} \text{ n}_{eq}/\text{cm}^2$ (10 μm pitch) & $2 \cdot 10^{12} \text{ n}_{eq}/\text{cm}^2$ (20 μm pitch)



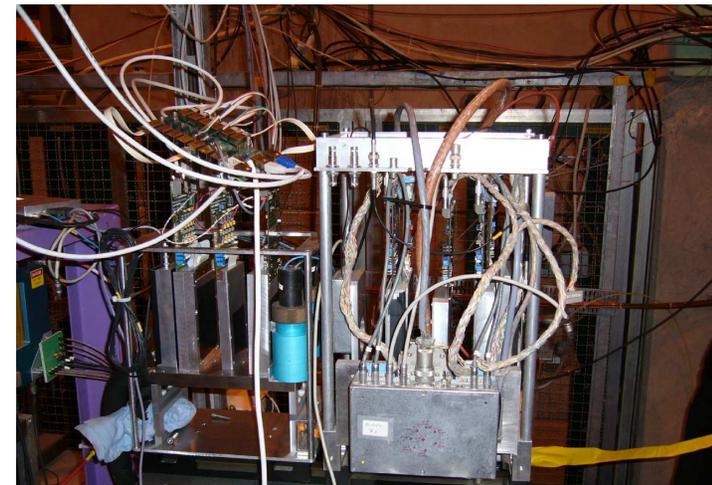
● Beam telescope of the FP6 project EUDET

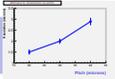
- * 2 arms of 3 planes (plus 1 high resolution plane)
- * $\sigma_{extrapol.} \lesssim 1 \mu m$ EVEN with e^- (3 GeV, DESY)
- * frame read-out frequency $O(10^2)$ Hz
- * running since '07 CERN-SPS & DESY (numerous users)
- * evolution towards 10^4 frames/s in 2009, using binary output sensors (see later)



● Several other applications :

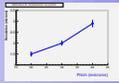
- * MIMOSA sensor R&D : Pixel Telescope of Strasbourg (TAPI) \rightarrow
- * STAR (RHIC) : telescope (3 MIMOSA-14) inside apparatus (2007)
 \rightarrow background measurement, no pick-up !
- * CBM (FAIR) : MVD demonstrator (double-sided layers) to be used for high precision tracking in HADES (GSI) \sim 2010
- * Spin-offs: β -imaging, hybrid photo-detectors, dosimetry, ...





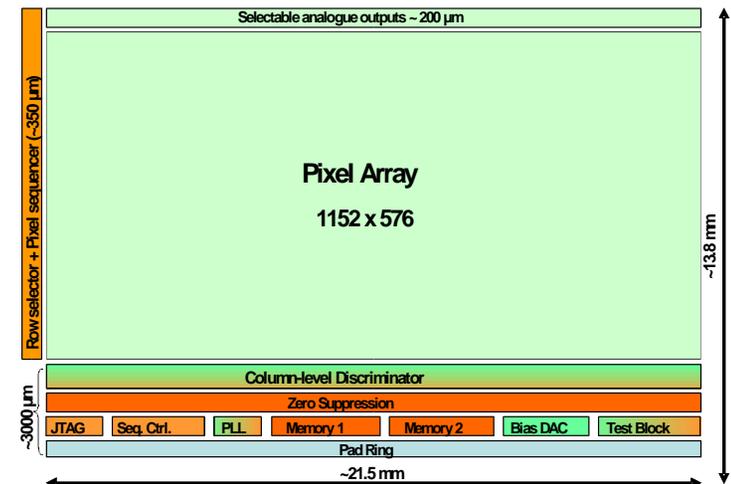
Improving the Read-Out Speed

with Digital Output Sensors



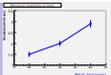
- TC \equiv 1st sensor with integrated zero-suppression

- * MIMOSA-22 (binary outputs) combined with \emptyset (SUZE-01)
- * Active area: 1152 columns of 576 pixels ($21.2 \times 10.6 \text{ mm}^2$)
- * Pitch: $18.4 \mu\text{m} \rightarrow \sim 0.7$ million pixels $\Rightarrow \sigma_{sp} \gtrsim 3.5 \mu\text{m}$
- * $T_{r.o.} \lesssim 110 \mu\text{s} \rightarrow \sim 10^4$ frames/s
 \Rightarrow suited to $> 10^6$ particles/cm²/s
- * \emptyset in 18 groups of 64 col. allowing ≤ 9 "pixel strings" / raw
- * Sensor full dimensions : $\sim 22 \times 14 \text{ mm}^2$
- * Data transmission: 1 output at ≥ 160 Mbits/s or 2 outputs at ≥ 80 Mbits/s



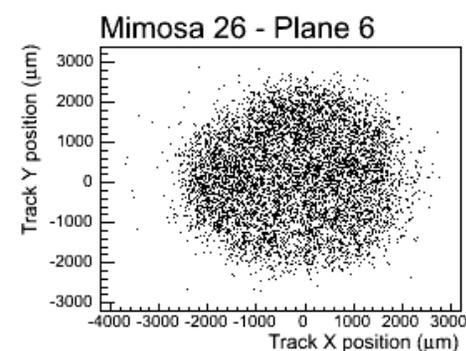
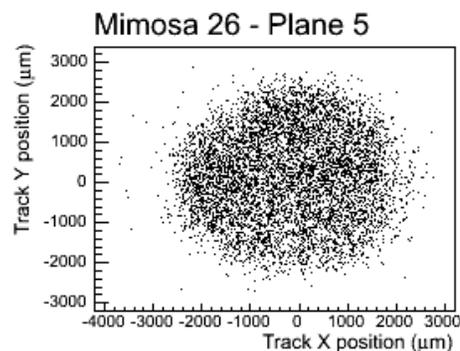
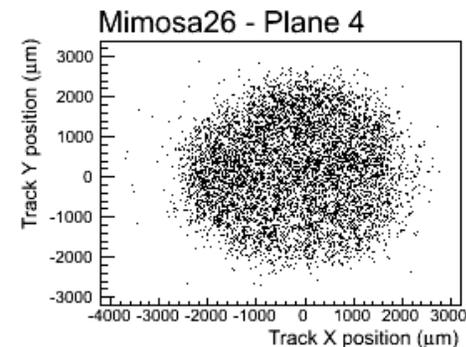
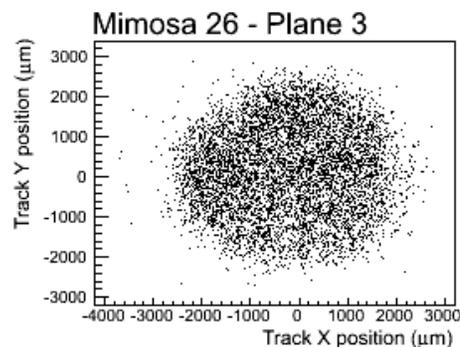
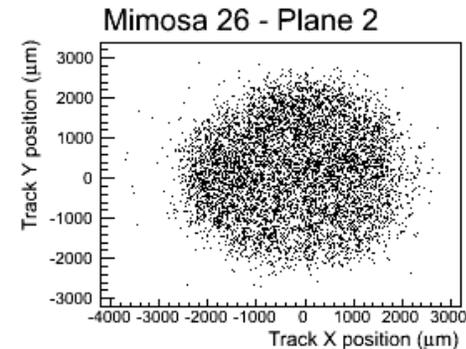
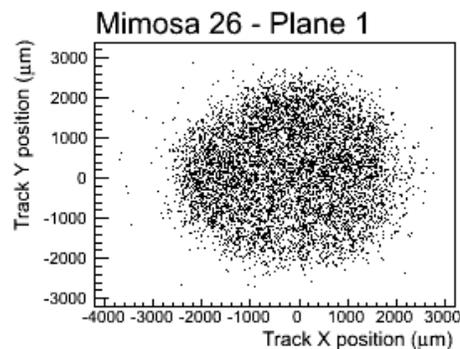
- Fabricated in $0.35 \mu\text{m}$ "Opto" technology:

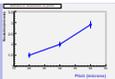
- * Equips the final version of EUDET Beam Telescope (EU-FP6 project)
- * Architecture is baseline for STAR, CBM and ILC vertex detectors (+ ALICE upgrade ?)
- * Sensor still being characterised \Rightarrow test results are **Preliminary**



- **6 sensors used:**
 - ✧ some thinned to $120\ \mu m$
 - ✧ assembled in telescope configuration
 - ✧ for minimum ionising particle detection performance evaluation

- **CRN-SPS (T4-H6)**
 - ✧ $\gtrsim 120\ \text{GeV}\ \pi^-$ beam
 - ✧ 10 days of run in Sept. 2009
 - ✧ 3×10^6 triggers collected, out of which $\sim 80\%$ events reconstructed

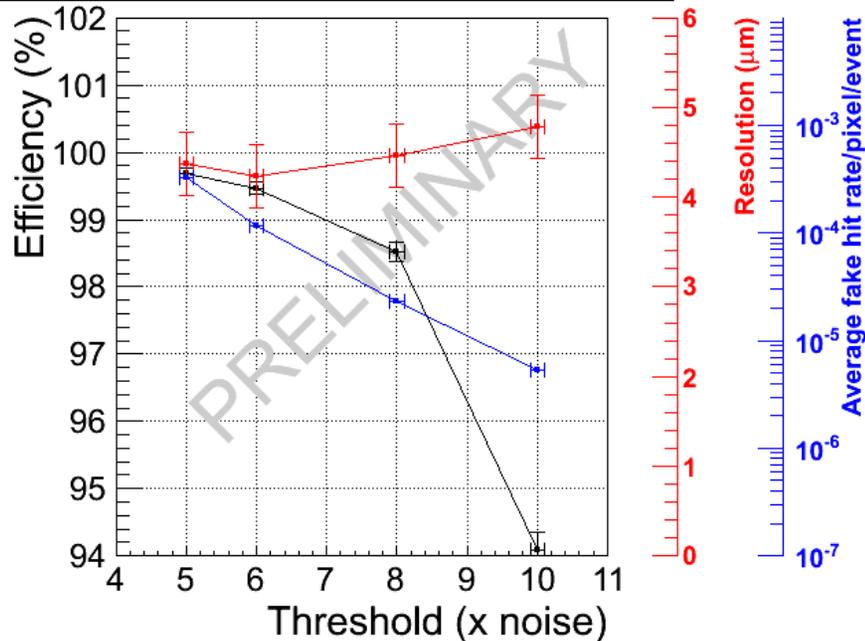




- TC sensors quite extensively characterised by now (quantitative results still preliminary):

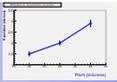
- * TC operating with $\gtrsim 99.5\%$ detection efficiency over the whole sensitive area, with a fake rate $\lesssim O(10^{-4})$
- * Optimal disc. threshold $\sim 5-6 \times$ Noise value
- * $\sigma_{sp}^{TC} \lesssim 4.5 \pm 0.2 \mu m$ (preliminary)
 \hookrightarrow room for improvement towards $\sigma_{sp}^{TC} \lesssim 4 \mu m$

MIMOSA 26 (chip 1) unthinned, vref2=98, 80 MHz

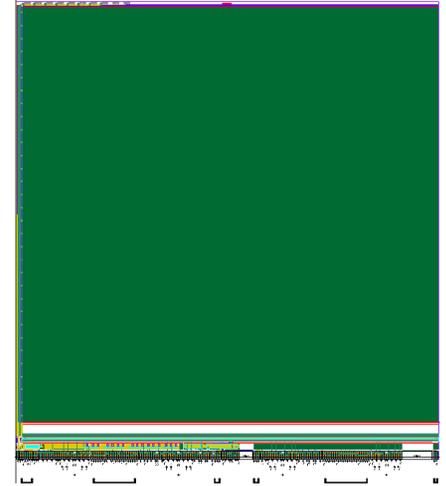


- Conclusion:

- * TC operational for the final EUDET BT ✓
- * TC architecture validated for devt of application specific sensors:
 - ▷ STAR-PIXEL, CBM-MVD, ILD-VTX, ... ALICE-ITS ?

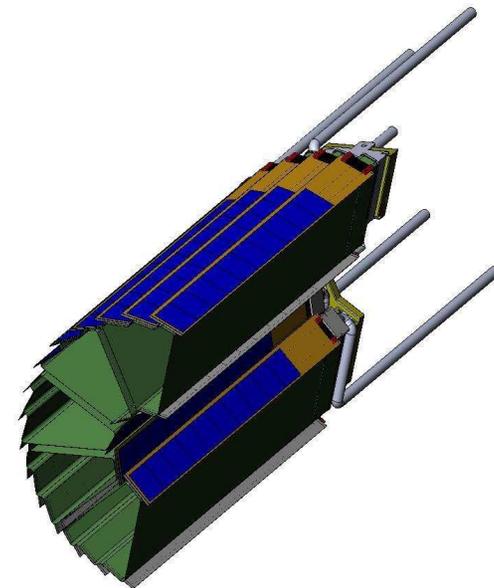


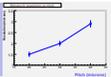
- **1st generation sensor for the HFT-PIXEL of STAR (PHASE-1):**
 - ✧ **full scale extension of MIMOSA-22 (no \emptyset)**
 - ✧ *640x640 pixels (30 μm pitch) \Rightarrow active surface: 19.2 x 19.2 mm²*
 - ✧ *integration time : 640 μs*
 - ✧ *designed and fabricated in 2008 \rightarrow currently under production test at LBNL*
 - ✧ *3 + 9 ladders to equip with 10 sensors thinned to 50 μm (1/4 of PIXEL)*
 - ✧ *1st physics data expected in 2011/12*



- **Final HFT-PIXEL sensor :**

- ✧ **MIMOSA-26 with active area \times 1.8**
& improved rad. tolerance
 - \hookrightarrow 1088 col. of 10^3 pixels (20 x 18.5 mm²)
- ✧ **Pitch : 18.4/20.7 μm \rightarrow \sim 1 million pixels**
- ✧ **Integration time \lesssim 200 μs**
- ✧ *Design in 2009/10 \rightarrow fab. Q4 (2010)*
 - \rightarrow *1st physics data expected in 2013/14*

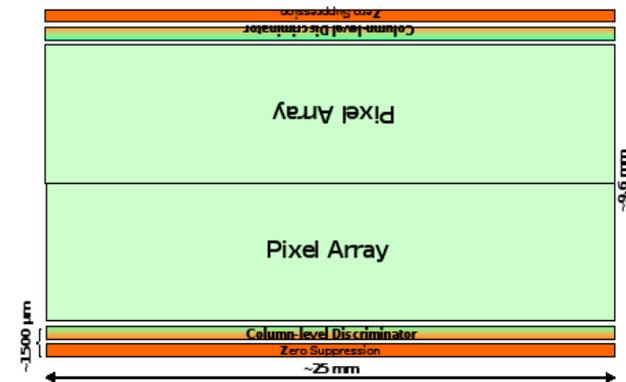




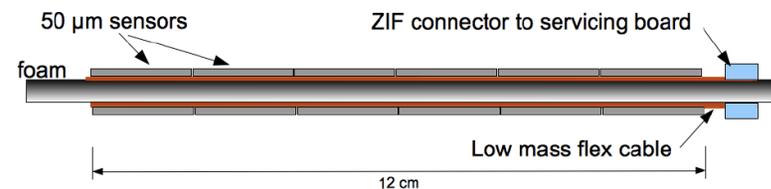
From TC to Faster Devices

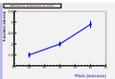
- Move from $0.35 \mu m$ to feature size $\leq 0.18 \mu m$
 - \Rightarrow improved clock frequency, more metal layers, more compact peripheral circuitry, etc.

- ILD VTX inner layers ($t_{int} \sim 25 - 50 \mu s$):
 - * double-sided r.o. \Rightarrow twice shorter (= faster) columns
 - * pitch $\lesssim 15 \mu m$
 - * binary r.o. $\Rightarrow \sigma_{sp} \lesssim 3 \mu m$



- Implement elongated pixels on one side of double-ladder:
 - * pixel pitch of $\sim 14 \times 50-80 \mu m$
 - * reduced nb of pixels per column
 - \Rightarrow shorter read-out (goal: factor 4-6)
 - * depleted epitaxial layer
 - \Rightarrow wider sensing diode spacing (next slide)
 - $\hookrightarrow \lesssim 10 \mu s$ may be reachable





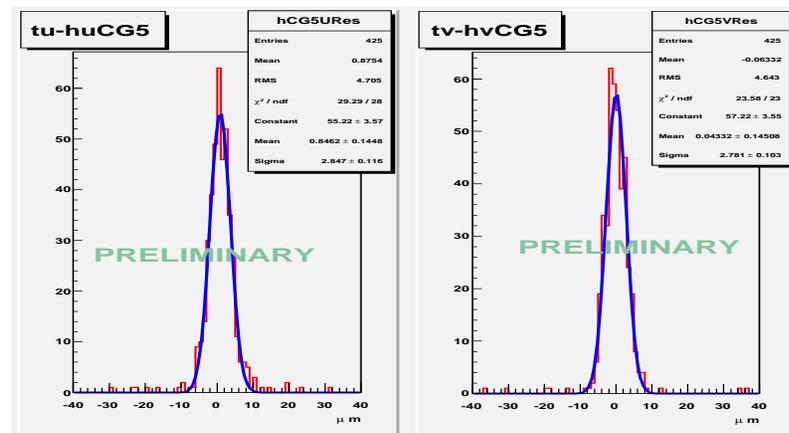
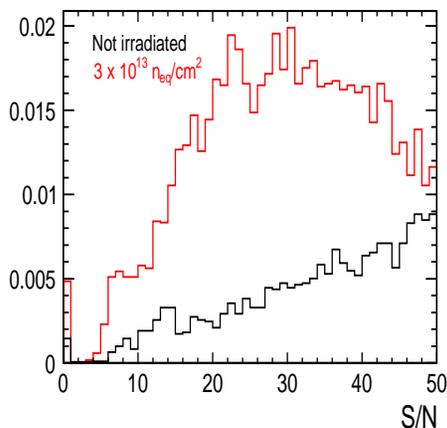
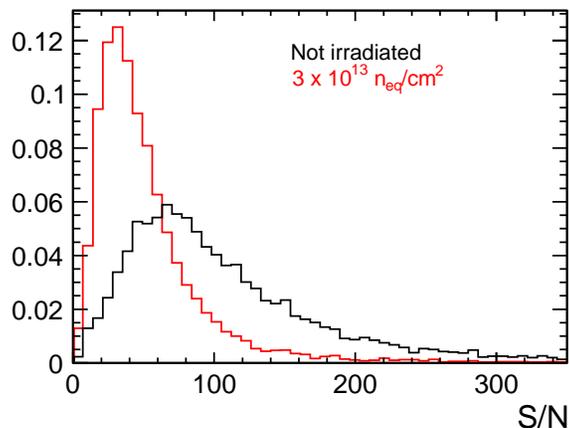
High Resistivity Sensitive Volume

- Advantages of depleted epitaxial layer:

- ✧ faster charge collection ($< 10\text{ ns}$) \Rightarrow faster frame read-out frequency possible
- ✧ shorter minority charge carrier path length \Rightarrow improved tolerance to non-ionising radiation

- Exploration of $0.6\ \mu\text{m}$ techno: $\sim 15\ \mu\text{m}$ thick epitaxy ; $V_{dd} \leq 5\text{ V}$; $\rho \sim O(10^3)\ \Omega \cdot \text{cm}$

- ✧ MIMOSA-25: fabricated in 2008 & tested at CERN-SPS before/after $O(1\text{ MeV})$ neutron irradiation



- Effect of $3 \cdot 10^{13}\ n_{eq}/\text{cm}^2$ at room temperature:

- ✧ SNR(MPV): $\sim 60 \searrow \sim 30 \triangleright \epsilon_{det}: 99.9\% \searrow 99.5\%$ at T_{room} with $20\ \mu\text{m}$ pitch & $80\ \mu\text{s}$ r.o. time
- \Rightarrow thin depleted epitaxy approach validated for $\gtrsim 10^{14}\ n_{eq}/\text{cm}^2 \triangleright 0.35\ \mu\text{m}$ version available soon

$$(\sigma_{sp} \sim 2.5 \pm 0.2\ \mu\text{m})$$

- Exploration of a new VDSM techno. with depleted substrate : project LePIX (organised by CERN)

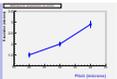
- \triangleright aim for very short integration time



- **Explore newly available 0.35 μm High-Resistivity technology:**
 - ✧ *resistivities: 400 and 200 $\Omega \cdot cm$*
 - ✧ *epitaxial thickness: 10, 15, 20 μm*
 - ✧ *TC/MIMOSA-26 begin refabricated on various substrates*
 - ✧ *multi-project run in February for STAR:*
 - *larger pitch \Rightarrow reduced power dissipation and r.o. time*
 - *reduced steering voltage \Rightarrow reduced power dissipation*
 - *improved amplification gain \Rightarrow enhanced SNR*
 - *improved ionising radiation tolerance of in-pixel amplification circuitry*

- **Explore 0.35 μm techno. extrapolated from the former 0.6 μm techno.**
 - ✧ *non-uniform resistivity (0.5 to 2 $k\Omega \cdot cm$) and only 3 metal layers*
 - ✧ *imaging device to be fabricated in Spring 2010*

- **Explore VDSM techno. with high-resistivity substrate & deep depletion potential (HV)**
 - ✧ *assess charge coll. properties, radiation tolerance, thinning (& post-processing) possibilities, etc.*
 - ✧ *envisage using this process for charge sensing in a 3D device (see later)*

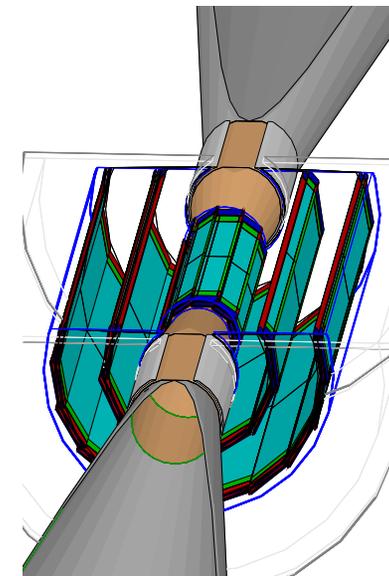


● PLUME project

≡ Pixelated Ladder using Ultra-light Material Embedding

● Objectives :

- * achieve a double-sided ladder prototype for an ILC vertex detector by 2012
- * evaluate benefits of 2-sided concept (mini-vectors) :
 σ_{sp} , alignment, shallow angle pointing, elongated vs square pixels

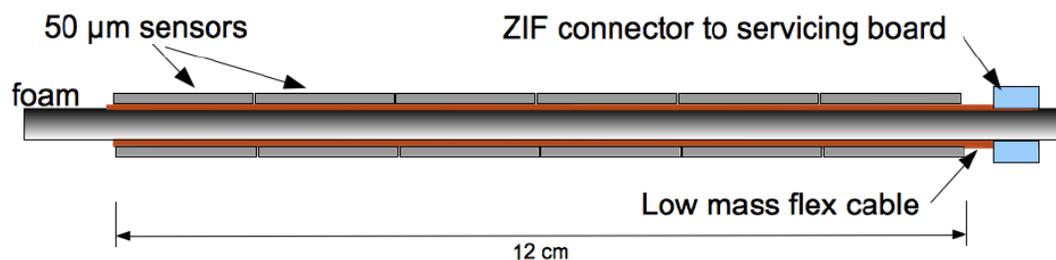


● Collaboration:

- * Bristol - DESY - Oxford - Strasbourg
- * Synergy with Vertex Detector of CBM/FAIR

● Perspective:

- * to be studied with infrastructure foreseen in FP-7 project AIDA (proposal in preparation)
- * interest for EIC experiments ?



- **HP-2 project** ▷ **WP-26 (ULISI)** ≡ **SEnsor Row Wrapped In an Extra-Thin Envelope (SERWIETE)**

- **Objectives :**

- * achieve a sensor assembly mounted on flex and wrapped in polymerised film with $\lesssim 0.15\%$ X_0 in total
- * evaluate possibility of mounting supportless ladder on cylindrical surface (serving as mechanical support)
- * proof of principle expected in 2012

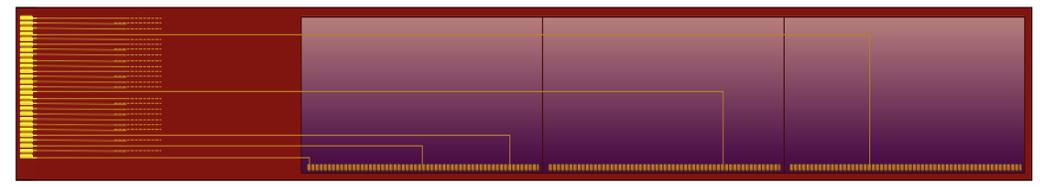
Proto 1 ▷ Spring 2010



- **Working programme:**

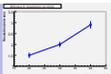
- * prototype Nr. 1 (2010) made of 1 sensor : MIMOSA-18 (analog output, $\lesssim 4$ ms)
- * prototype Nr. 2 (2011) made of 3 sensors : TC (digital output, $\lesssim 110 \mu s$)

Proto 2 ▷ Summer 2011



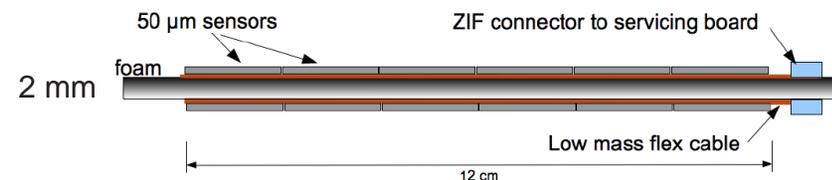
- **Context of development:**

- * Collaboration with IKF-Frankfurt and GSI/Darmstadt (CBM coll.)
- * Synergy with Vertex Detector R&D for CBM, ILC, etc.



■ Improve capability of displaced vertex reconstruction for charm tagging :

- Foresee a detector made of 3 double layers (barrel & end-cap ?)
(and envisage equipping beam pipe ???)



- Ambitionned performances:

- ✧ thin pixel sensors ($50 \mu m$) offering a single point resolution $\lesssim 5 \mu m$?
- ✧ ladder with complete material budget $\lesssim 0.3 \% X_0$
- ✧ 2 contiguous impacts per particle detected \Rightarrow several benefits for detection performances:
 - ◇ resolution (impact param.)
 - ◇ track rec.
 - ◇ alignment (crucial !)
 - ◇ speed ?

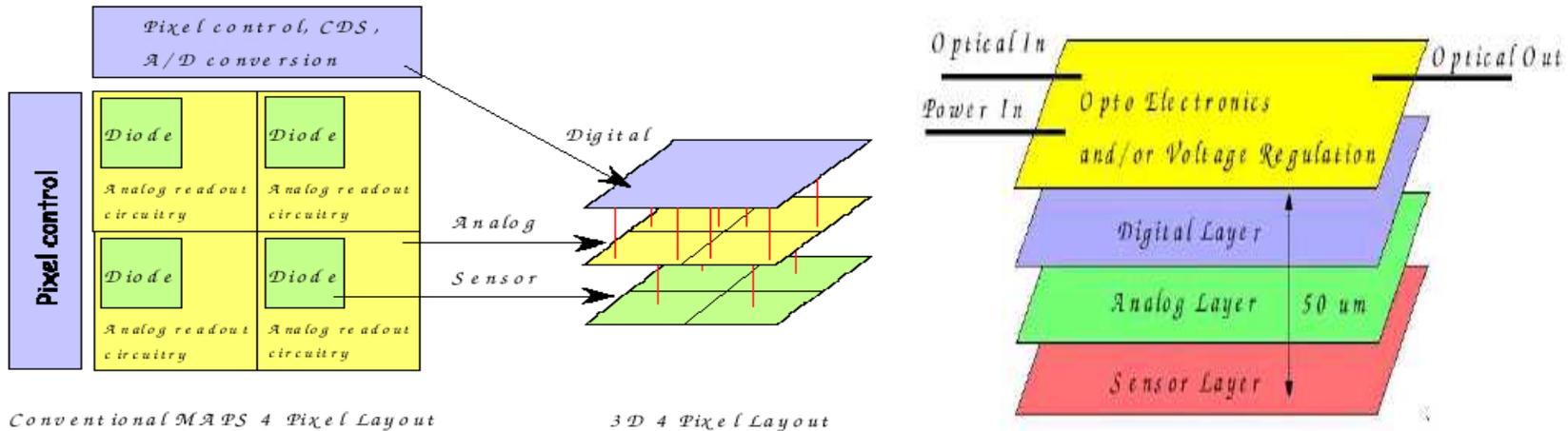
■ Context : R&D on-going at IPHC-Strasbourg

- Devt of thin, high resolution, CMOS pixel sensors for STAR & CBM (since 2000 & 2003)
 \Rightarrow design of sensor architecture \sim mature (sensor operational on EUDET/FP-6 telescope)
- Devt of ultra-light ladders for CBM, ILC, etc. (since 2008) \rightarrow WP-26 (HP-2)
 \Rightarrow several approaches investigated \rightarrow prototyping finalised \sim 2012/13
- First data collected with STAR-PIXEL (open charm) in 2012/13
 \Rightarrow single-sided ladders: $\sigma_{sp} \lesssim 5 \mu m$, material budget $\sim 0.3-0.4 \% X_0$

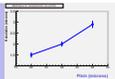


Using 3DIT to Improve CMOS Sensor Performances

- **3D Integration Techno.** allow integrating high density signal processing μ circuits inside small pixels by stacking ($\sim 10 \mu m$) thin tiers interconnected at pixel level
- **3DIT are expected to be particularly beneficial for CMOS sensors :**
 - ✧ combine different fab. processes \Rightarrow chose best one for each tier/functionnality
 - ✧ alleviate constraints on peripheral circuitry and on transistor type inside pixel, etc.
- **Split signal collection and processing fonctionnalities :**
 - ✧ *Tier-1: charge sensing*
 - ✧ *Tier-2: analog-mixed μ circuits*
 - ✧ *Tier-3: digital μ circuits*



- **First chips fabricated in 2009 within 3DIC Consortium (2-Tier 130 nm technology):**
 - ✧ 1 chip with sensitive area subdivided in "small" matrices running INDIVIDUALLY in fast rolling shutter mode \Rightarrow few μs r.o. time may be reached (?)
 - ✧ 1 chip aiming to combine 2-Tier read-out chip with sensing chip featuring DEPLETED epitaxial layer

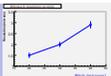


■ CMOS pixel sensors :

- Ambitionned performances (room T):
 - * $\sigma < 5 \mu m$ ✓
 - * thickness $\lesssim 50 \mu m$ ✓
 - * $t_{ro} \sim 10-20 \mu s$
 - * 1 MRad & $10^{14} n_{eq}/cm^2$
 - \Rightarrow on-going R&D on t_{ro} ($< 50 \mu s$) & rad. tolerance (> 300 kRad & $\gg 10^{13} n_{eq}/cm^2$)
- 3 sensor generations under development:
 - * 2D with undepleted sensitive volume $\rightarrow t_{ro} \sim 10-20 \mu s$ & 1 MRad (2011/12)
 - * 2D with depleted sensitive volume (elongated pixels) \rightarrow 1 MRad & $10^{14} n_{eq}/cm^2$ (2013)
 - * 3D with depleted sensitive volume $\rightarrow t_{ro} \lesssim 5 \mu s$ (2015)

■ Ladder developed along 2 parallel approaches:

- Classical : sensors \oplus flex cable \oplus SiC foam \oplus flex cable \oplus sensors
 - $\Rightarrow \lesssim 0.3 \% X_0$ for the whole 2-sided ladder
- Innovating : sensors ($35 \mu m$) wrapped in polymerised film ($\lesssim 10 \mu m$)
 - $\Rightarrow \lesssim 0.15 \% X_0$ for 1 unsupported layer (sensors \oplus flex cable \oplus film)
 - \hookrightarrow adaptable to various mechanical supports \rightarrow beam pipe ?



- **Proposal: investigate possibility of translating ultra-light pixelated ladders developed for CBM & ILC to the specifications of an EIC vertex detector, relying on 2 basic components:**
 - ✧ thin, depleted, CMOS pixel sensors (baseline 2D, potentially 3D)
 - ✧ ultra-light double-sided ladder complemented with potential pixelated beam pipe
- **CMOS pixel sensors developed for EUDET, STAR, CBM, ILC, ALICE (?):**
 - ✧ offer necessary single point resolution and material budget for very high precision vertexing
 - ✧ have reached required maturity to be used in large (heavy ion) experiments (e.g. STAR-HFT)
 - ⇒ may be relevant for an EIC vertex detector > 2015: barrel & forward (CBM-MVD)
- **Ultra-light ladders developed for CBM & ILC:**
 - ✧ double-sided ladder with $\lesssim 0.3 \% X_0$, expected to provide excellent pointing accuracy: impact parameter resolution even at shallow angle, track link with faster detectors, ...
 - ✧ supportless ladder expected to offer $\lesssim 0.15 \% X_0 \rightarrow$ explore possibility to equip beam pipe ?
- **Synergetic context to exploit:**
 - ✧ CMOS sensor development with Heavy Ion Community
 - ✧ ladder development within HP-2 (Frankfurt, GSI), PLUME collaboration (ILC teams)
 - ✧ perspective: AIDA FP-7 proposal (study of high precision vertex detector alignment issues)